

Silicon NPN Power Transistors

2SD882

DESCRIPTION

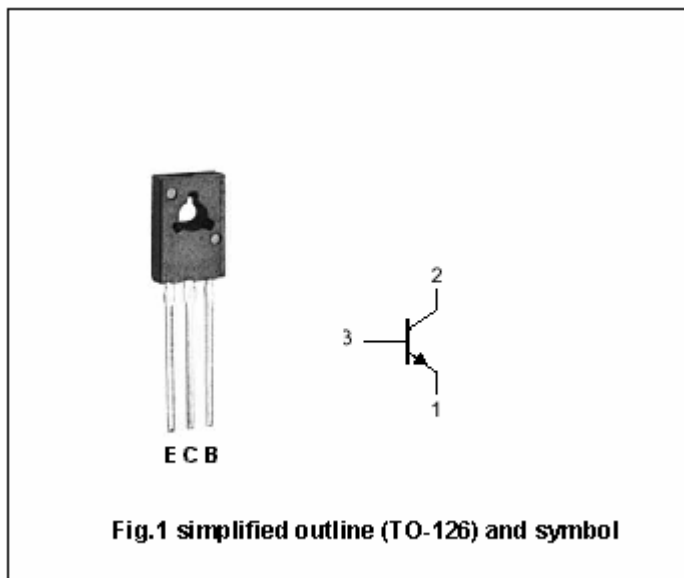
- With TO-126 package
- Complement to type 2SB772

APPLICATIONS

- Audio amplifier
- Voltage regulator
- DC-DC converter
- Relay driver

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	40	V
V _{CEO}	Collector-emitter voltage	Open base	30	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current (DC)		3	A
I _{CM}	Collector current-peak		7	A
P _D	Total power dissipation	T _a =25°C	1	W
		T _c =25°C	10	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	30			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2.0A; I _B =0.2A			0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2.0A ; I _B =0.2A			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =30V; I _E =0			1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =3V; I _C =0			1	μA
h _{FE-1}	DC current gain	I _C =20mA ; V _{CE} =2V	30			
h _{FE-2}	DC current gain	I _C =1A ; V _{CE} =2V	60		400	
f _T	Transition frequency	I _C =0.1A ; V _{CE} =5V		90		MHz
C _{OB}	Collector output capacitance	f=1MHz ; V _{CB} =10V		45		pF

◆ h_{FE-2} Classifications

R	Q	P	E
60-120	100-200	160-320	200-400

PACKAGE OUTLINE

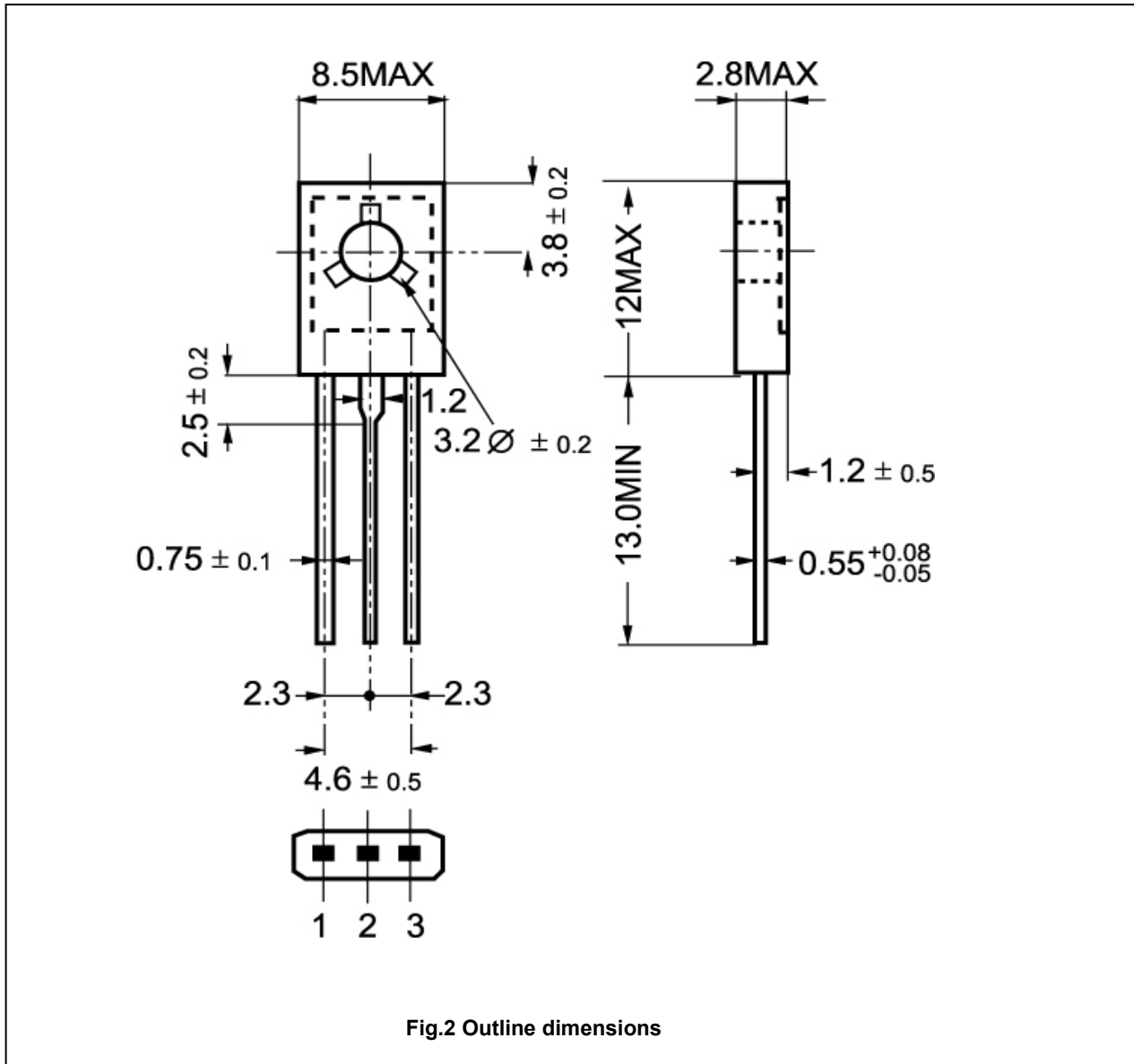


Fig.2 Outline dimensions

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